



KKR-CPA method tutorial (MACHIKANEYAMA2002)

The 35th CMD workshop at Osaka Univ.
Toyonaka Campus



Material design: application of machikaneyama

Spintronics materials

- Design of ZB-type half-metals (CrAs etc.)
- Design of half-metallic half-Heusler alloy
- Design of dilute magnetic semiconductors (DMS)
- Design of full-Heusler alloy (effect of disorder)

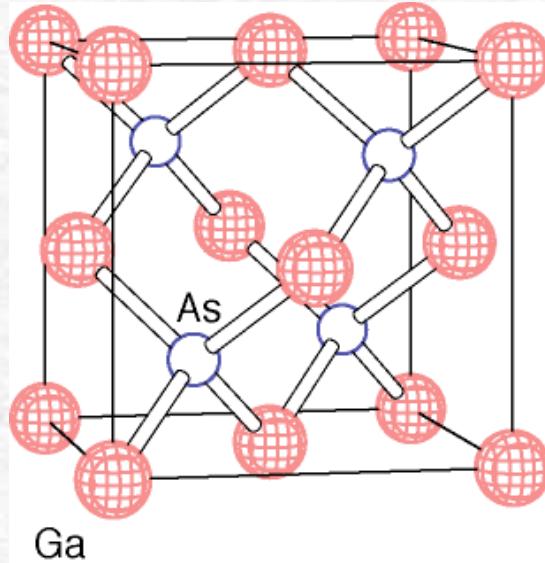
Li-ion battery electrode

- LiCoO_2
- Design of positive electrode material

Hydrogen Storage material

- Design of MgH_2 based materials

Half-metallic CrAs

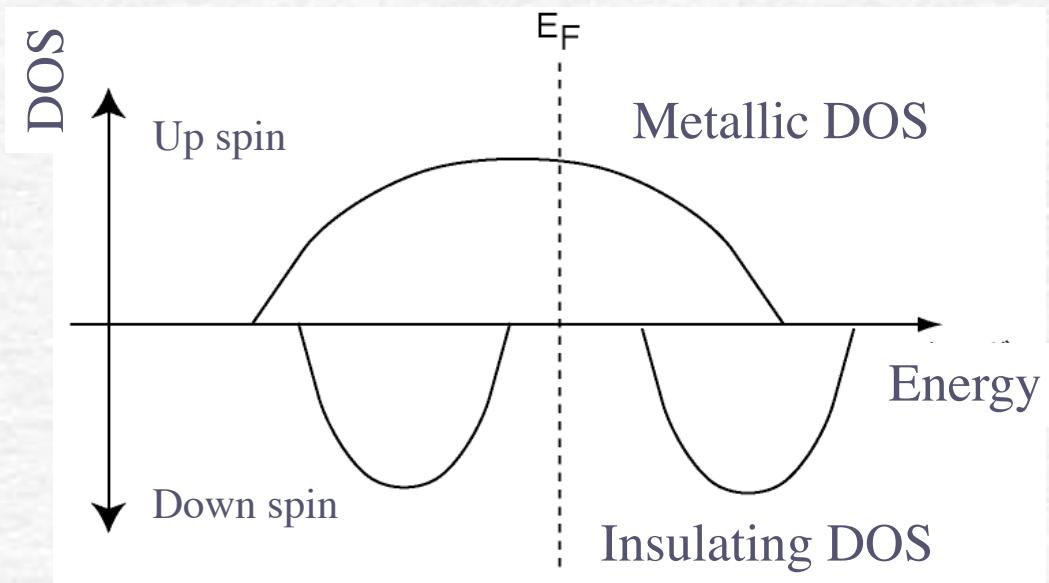


Zinc blende structure

GaP, GaAs, GaSb,
ZnS, ZnSe, ZnTe

Shirai et al. predicted zinc-blende CrAs is **half-metallic ferromagnet**
From first-principles calculations. Akinaga et al. confirmed
this prediction experimentally later.
(Jpn. J. Appl. Phys. 39 (2000) L1118)

Half-metallic ferromagnet



100 % spin polarization at the Fermi level.
Expected as a spin polarizer for semiconductor spintronics.

Explore half-metallic ferromagnets

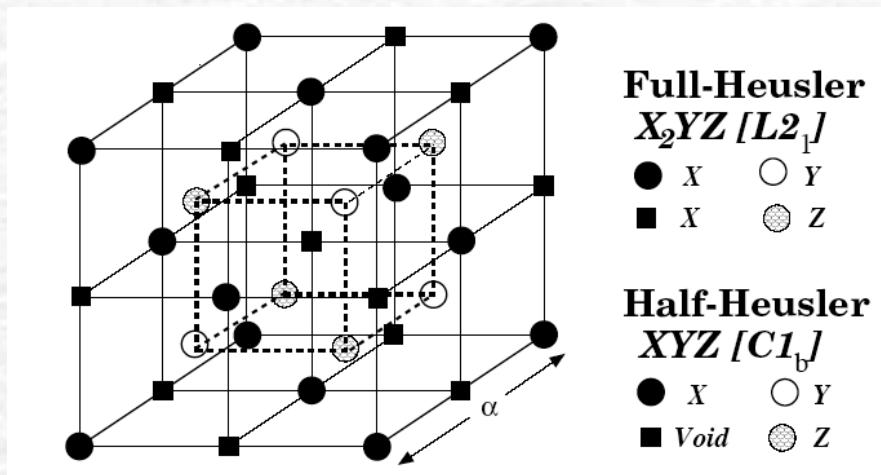
1. CrAs
 - DOS, magnetic moment, half-metallicity, T_C
2. With transition metals other than Cr (such as V, Mn ...)
3. With anions other than As (such as N, P, Sb, S, Se, Te ...)
4. How large T_C values are expected ?
5. Lattice constant dependence ?
 - Suppose different substrate
 - Calculate theoretical lattice constant. Half-metallic ?

Material design of half-metallic compounds with zinc-blende structure

	4.98 Å (InN)	5.45 Å (GaP)	5.65 Å (GaAs)	5.87 Å (InP)	6.06 Å (InAs)	6.10 Å (GaSb)	6.48 Å (InSb)
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CrP							
CrAs							
CrSb							
MnP							
MnAs							
MnSb							
VP							
VAs							
VSb							

Heusler alloy



Composed with FCC sub-lattices
(similar to the zinc blende structure)

- Full Heusler
 - Co₂MnSi ...
 - Half-metallic, $T_C=985$ K
- Half Heusler
 - NiMnSb ($a = 5.93$ Å)
 - Half-metallic, $T_C=730$ K

Various combinations of transition metals.

Systematic study on the electronic structure, magnetic moment, T_C

Slater-Pauling curve of Half-Heusler alloy

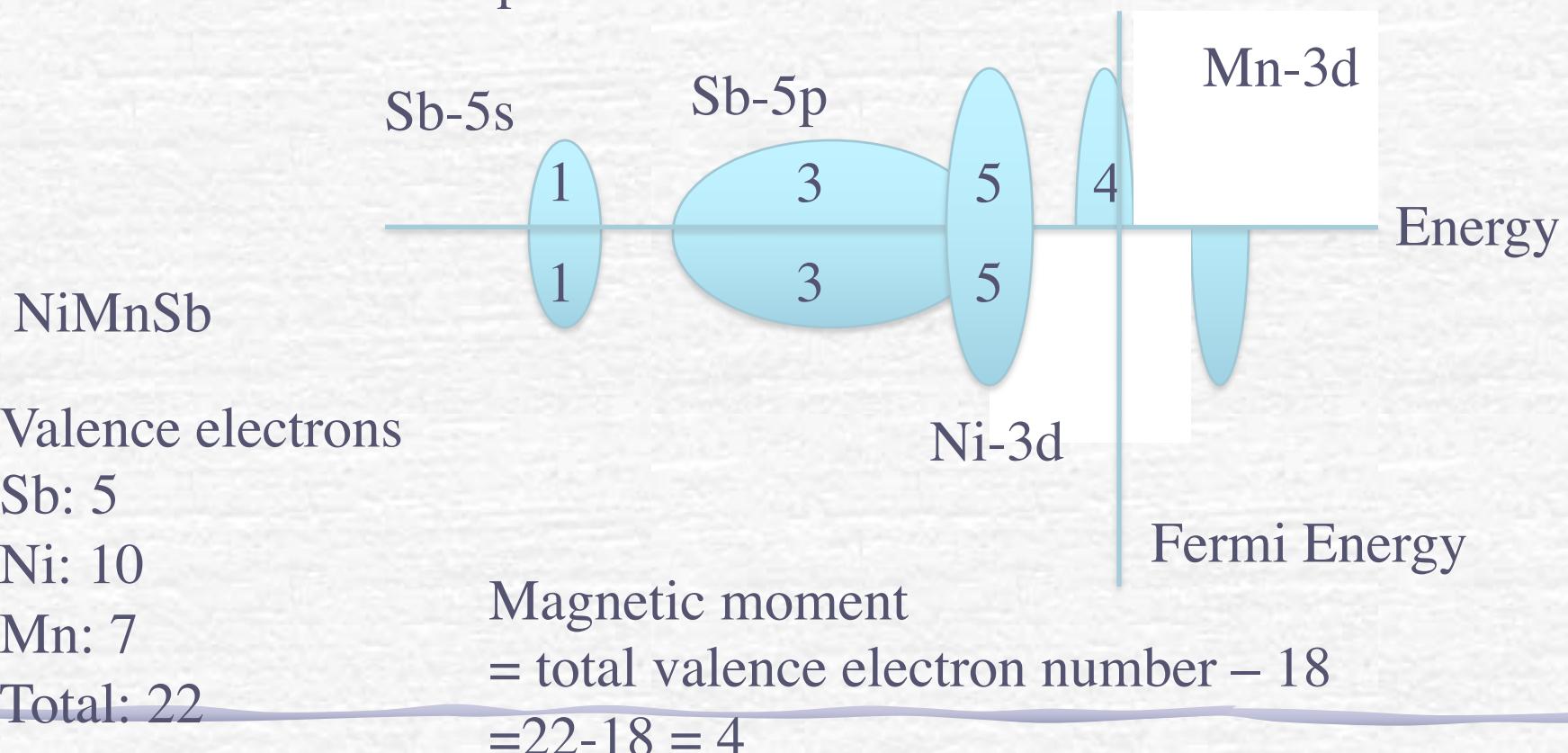
1. NiMnSb、CoMnSb、FeMnSb
 - DOS, magnetic moment, half-metallicity
 - Estimate T_C
2. Magnetic moment vs. total valence electron number
 - Slater-Pauling curve,
 - Guess how large magnetic moment is expected for different combinations
 - Confirm the above expectation by ab-initio calculation.
 - Is it also true in ,e.g., $(Ni_{1-x}Co_x)MnSb$?
3. New ferromagnets based on semiconducting Half-Heusler alloy
 - Predict semiconducting Half-Heusler alloy based on the
 - Dope magnetic impurities Co(Ti, Mn)Sb

Half-metallic half-Heusler alloy

XYSn (50)	Element at site Y			
	Ti (22)	V (23)	Cr (24)	Mn(25)
X	Ni(28)			
	Co(27)			
	Fe(26)			
	Pd(46)			
	Rh(45)			
	Ru(44)			

Schematic density of state of half-Heusler alloy

18 electrons are needed
to fill up the valence band



Carrier induced ferromagnetism in DMS

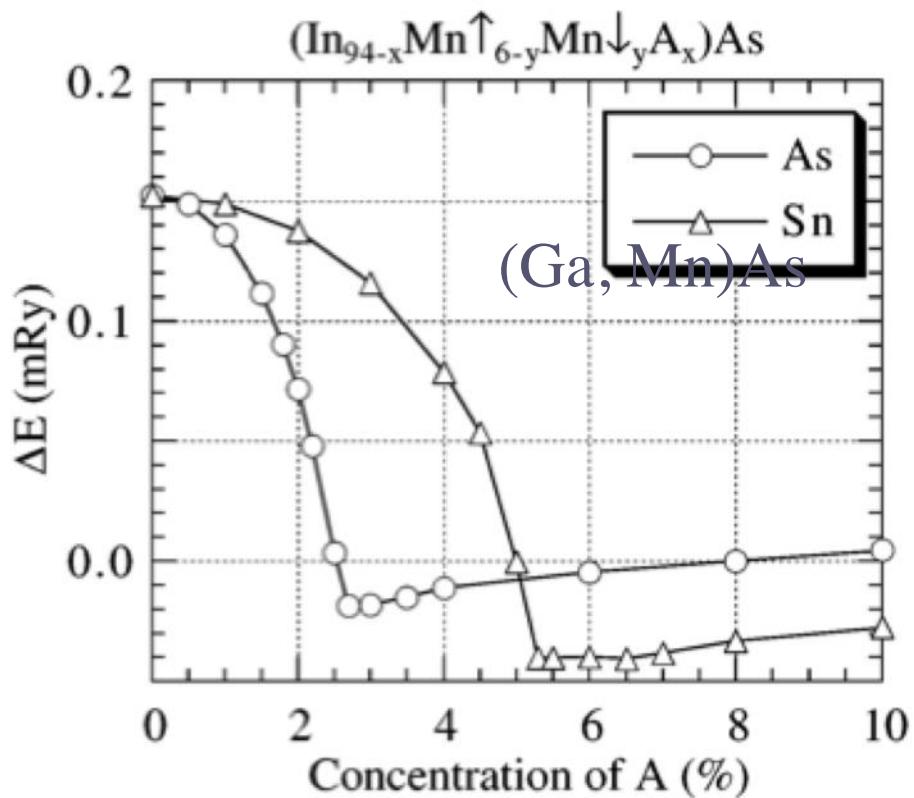


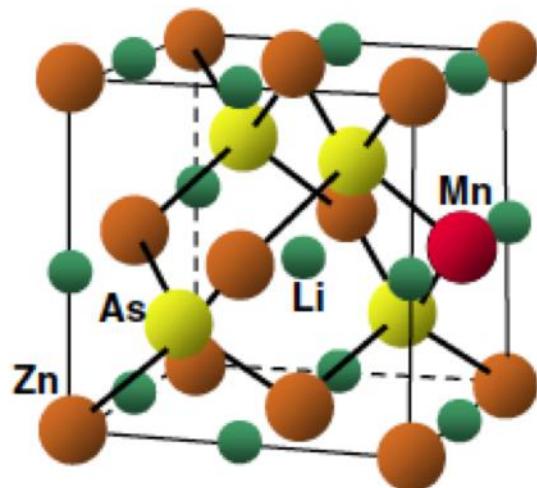
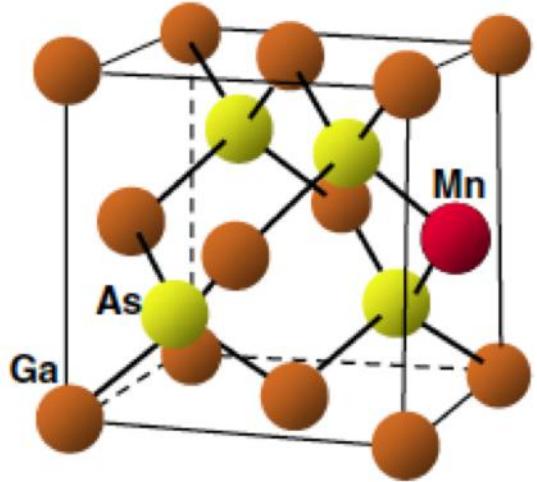
FIG. 3. The difference $\Delta E = E_{\text{LMD}} - E_{\text{ferro}}$ in the total energy between $(\text{In}_{0.94-x}\text{Mn}^{\uparrow}{}_{0.03}\text{Mn}^{\downarrow}{}_{0.03}\text{A}_x)\text{As}$ and $(\text{In}_{0.94-x} \times \text{Mn}^{\uparrow}{}_{0.06}\text{Mn}^{\downarrow}{}_{0}\text{A}_x)\text{As}$ as a function of the concentration x of $A = \text{As}$ or Sn at the antisite.



- Dilute magnetic semiconductors (DMS)
 - $(\text{Ga}, \text{Mn})\text{As}$, $(\text{In}, \text{Mn})\text{As}$..
 - Ferromagnetic material
 - Ferromagnetism controllable by changing carrier density
 - Semiconductor spintronics
- High-Tc DMS necessary
 - High concentration doping crucial
- Material design

Filled tetrahedral semiconductors LiZnAs

Masek et al., PRL 98 (2007) 067202

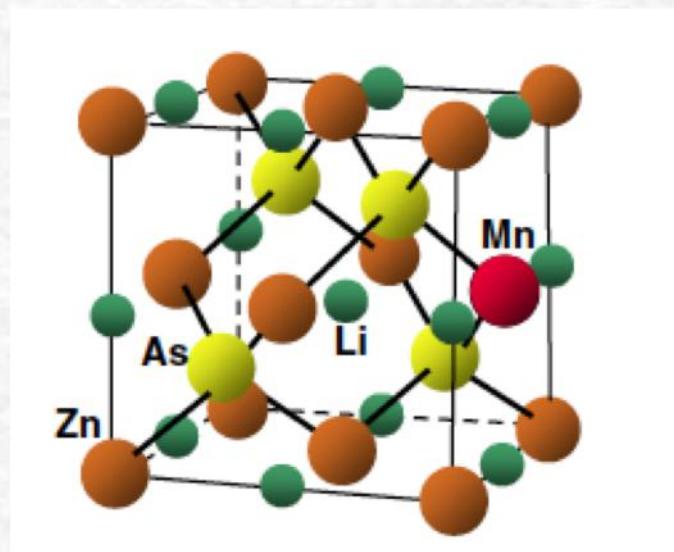


- ☞ Zinc blende structure + interstitial Li (Half-Heusler)
- ☞ $\text{Ga}^{3+}\text{As}^{3-}$
⇒ $\text{Zn}^{2+}\text{As}^{3-} + \text{Li}^{1+}$
- ☞ $\text{Zn}^{2+} \Rightarrow \text{Mn}^{2+}$: High solubility
 - $E_{\text{Form}}(\text{Mn}_{\text{Zn}} \text{ in LiZnAs}) = \sim -3 \text{ (eV)}$
 - $E_{\text{Form}}(\text{Mn}_{\text{Ga}} \text{ in GaAs}) = \sim +1 \text{ (eV)}$
- ☞ Carrier control by Li addition (removal)

Mahadevan et al., PRB 68 (2003) 075202.

Juza et al., Angew. Chem. 7 (1968) 360
v. G. Achenbach et al., Z. Anorg. Allg. Chem. 476 (1981) 9.

Materials design of LiZnAs-DMS



Atomic position

- Zn: (0,0,0)
- As: (0.25, 0.25, 0.25)
- Li: (0.5, 0.5, 0.5)
- Vc: (0.75, 0.75, 0.75)
- Lattice constant $a = 4.955 \text{ \AA}$

Carrier doping

- Hole: Li vacancy
- Electron Li interstitial
- Calculate DOS

Mn doping

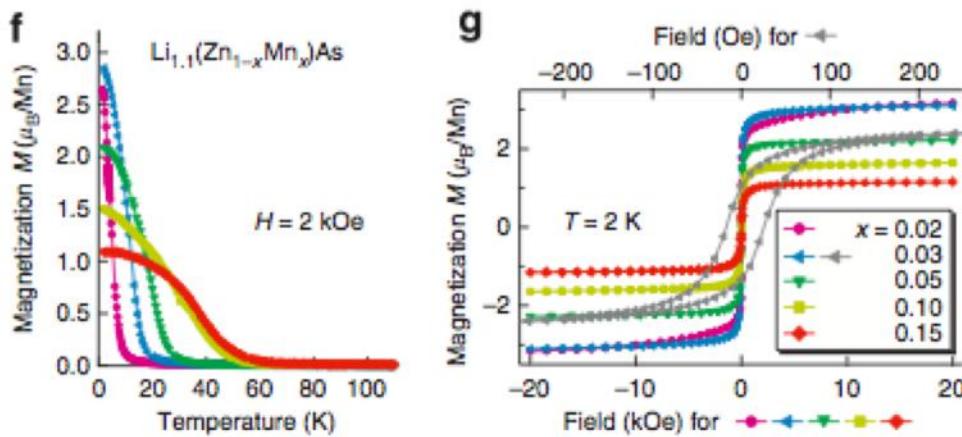
- DOS
- Curie temperature
- Carrier concentration dependence

Carrier induced ferromagnetism in Li(Zn, Mn)As

Hole doping		0%	5%	10%	15%	20%	25%
Mn conc.	5%						
	10%						
	15%						
	20%						
Electron doping		0%	5%	10%	15%	20%	25%
Mn conc.	5%						
	10%						
	15%						
	20%						

Recent experiment

Z. Deng et al., Nature Commun.
2:422, (2011, Aug.) 1-5.



- Solid-state reaction
- XRD
- dc-magnetization, μSR
- Hall effect $\Rightarrow p$ -type
- Li at Zn substitutional site

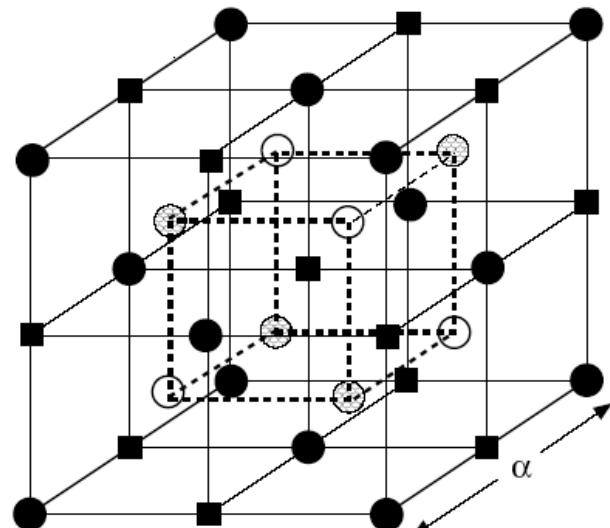
Table 1 | Ferromagnetic transition temperature and ordered moment size.

Li concentration	1.05		1.1		1.2	
	T_c (K)	M ($T=2 \text{ K}$)	T_c (K)	M ($T=2 \text{ K}$)	T_c (K)	M ($T=2 \text{ K}$)
<i>Mn concentration</i>						
0.03			17	2.9		
0.05			29	2.1	14	1.8
0.1	22	0.6	49	1.5	22	1.4
0.15	38	0.5	50	1.1	23	0.7

M (Bohr magneton per Mn).

The values of T_c and the average ordered moment size M per Mn of $\text{Li}_{1+x}(\text{Zn}_{1-x}\text{Mn}_x)\text{As}$ at $T=2 \text{ K}$ and $H=2 \text{ kOe}$ derived from magnetization measurements for several combinations of Li and Mn concentrations.

Atomic Disorder in full Heusler alloys



Full-Heusler
 X_2YZ [$L2_1$]

● X ○ Y
■ X ○ Z

Half-Heusler
 XYZ [$C1_b$]

● X ○ Y
■ $Void$ ○ Z

$$Polarization = \frac{DOS^{\uparrow}(E_F) - DOS^{\downarrow}(E_F)}{DOS^{\uparrow}(E_F) + DOS^{\downarrow}(E_F)}$$

Co₂CrAl

Cr \leftrightarrow Al disorder

Cr \leftrightarrow Co disorder

- Half-metallicity
- Magnetic moment
- Spin polarization
- Total energy

$$Polarization = \frac{DOS^{\uparrow}(E_F) - DOS^{\downarrow}(E_F)}{DOS^{\uparrow}(E_F) + DOS^{\downarrow}(E_F)}$$

$\text{Co}_2(\text{Cr}_{1-y}\text{Al}_y)(\text{Al}_{1-y}\text{Cr}_y)$

y	Total energy (Ry)	Moment	Polarization
0			
0.05			
0.1			
0.15			
0.2			
0.25			
0.3			
0.35			
0.4			
0.45			
0.50			

$$Polarization = \frac{DOS^{\uparrow}(E_F) - DOS^{\downarrow}(E_F)}{DOS^{\uparrow}(E_F) + DOS^{\downarrow}(E_F)}$$

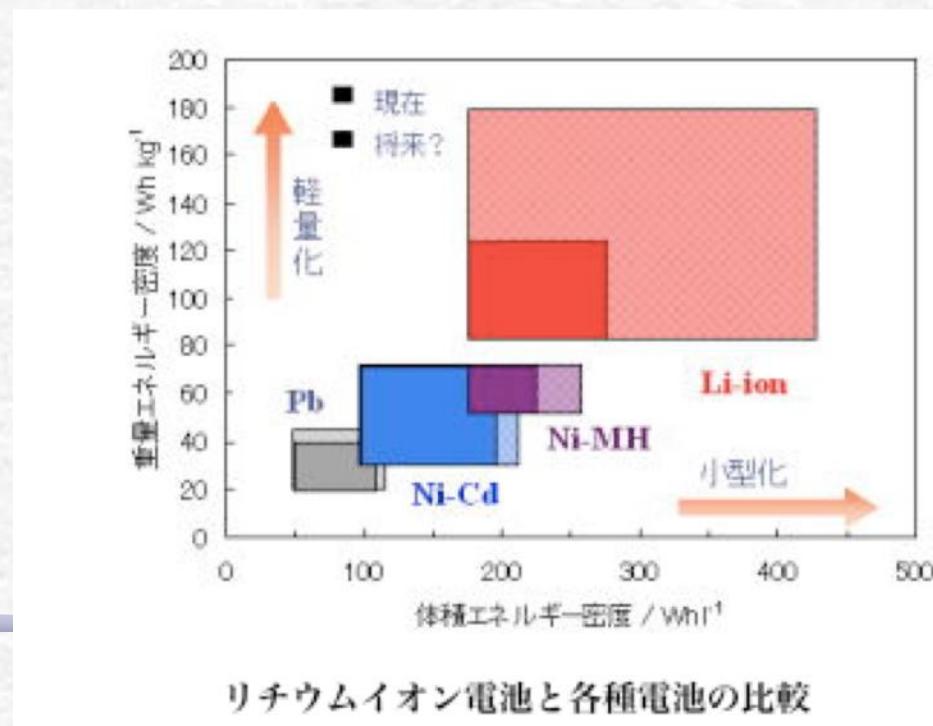


x	Total energy (Ry)	Moment	Polarization
0			
0.05			
0.1			
0.15			
0.2			
0.25			
0.3			
0.35			
0.4			
0.45			
0.47			
0.50			

Lithium-ion rechargeable battery

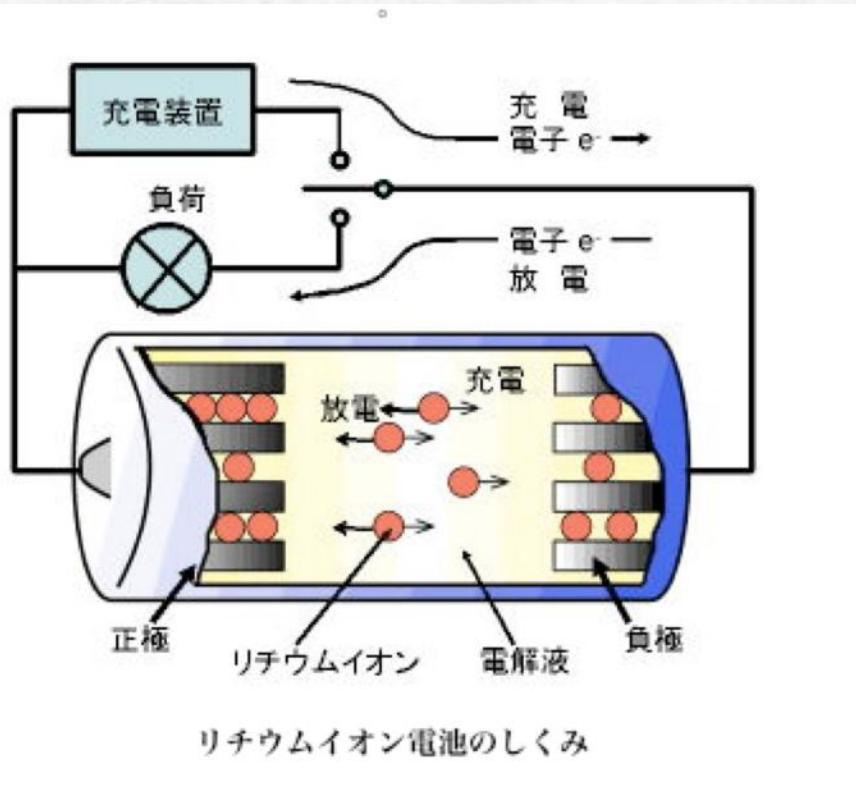
1. Rechargeable battery

- Chargeable, usable repeatedly
- Lead battery, Ni-Cd battery
- Li-ion battery, Ni-H battery (large energy density)



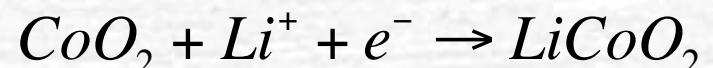
Design of positive and negative electrodes
for more effective
rechargeable battery

Lithium-ion rechargeable battery



- A. ‘good’ battery
1. High voltage
 2. Large capacity
 3. Low cost
 4. Light weight
 5. safety

Positive electrode :

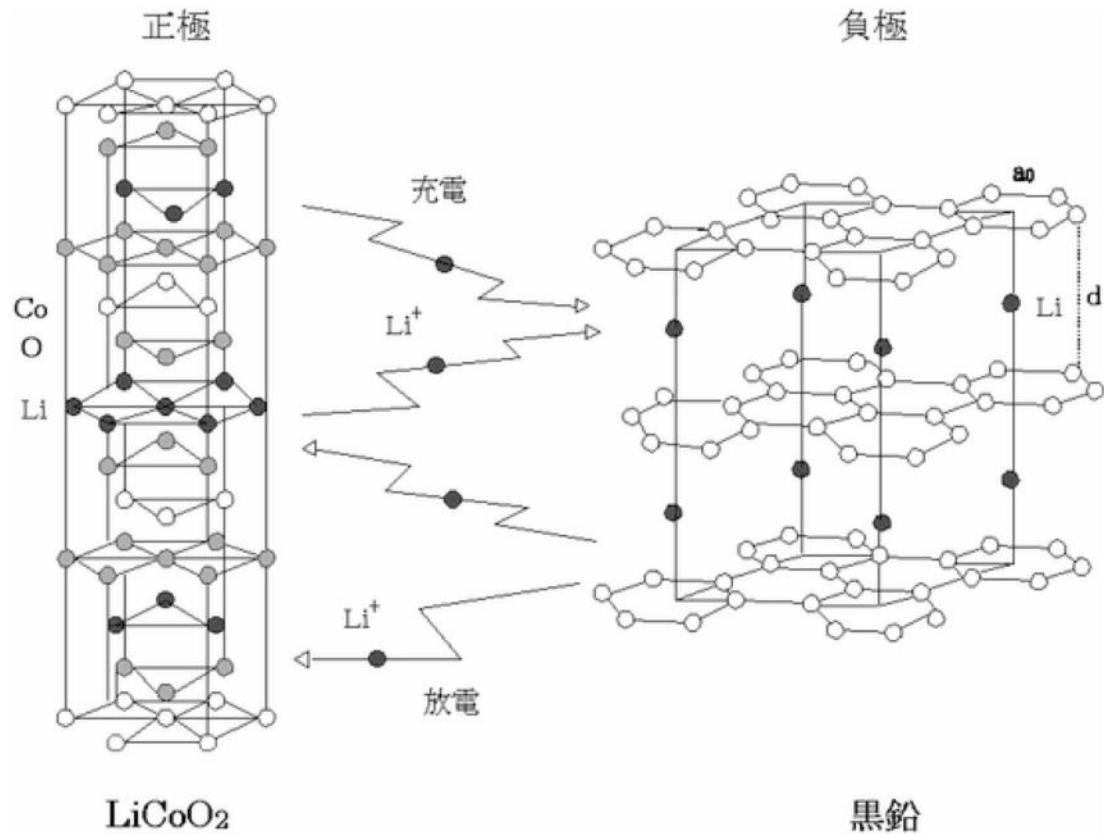


Negative electrode :



Total (discharging reaction) : $CoO_2 + Li \rightarrow LiCoO_2$

Positive electrode: LiCoO_2



1. Estimation of battery voltage
2. Negative electrode : Li metal
3. No lattice relaxation

Rhombohedral

R (TM): $(0,0,0)$

M (Li): $(1/2, \frac{1}{2}, \frac{1}{2})$

O: $(u, u, u), (-u, -u, -u)$

$$-V = TE(\text{LiCoO}_2) - TE(\text{CoO}_2) - TE(\text{Li})$$

Positive electrode: LiCoO_2

Co is very expensive → use the other transition metals for electrodes

	Ti	V	Cr	Mn	Fe	Co	Ni
¥/kg	2000	6000	400	310	30-90	8000	2000
toxicity	—	×	×	—	—	—	—

- Chemical trend of the battery voltage on TM ions
 LiTMO_2 , TM=Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn, Al
- Alloying works? Use much cheaper TM metals
 $\text{Li}(\text{Co, Al})\text{O}_2$, $\text{Li}(\text{Co, Zn})\text{O}_2$, $\text{Li}(\text{Co, Cu})\text{O}_2$
 $\text{Li}(\text{Ni, Mn})\text{O}_2$
 $\text{Li}(\text{Ni, Mn, Co})\text{O}_2$

Try to design positive electrode

TM	Tl(22)	V(23)	Cr(24)	Mn(25)	Fe(26)	Co(27)	Ni(28)
a (a.u.)	9.458	9.764	9.638	9.081	9.227	9.373	9.486
Alpha (deg)	34.64	31.90	33.12	35.37	34.17	32.97	33.37
Voltage (V)							

Metal	Cu(29)	Zn(30)	Al(13)	Sc(21)	B(5)
a (a.u.)	8.664	8.767	9.460		
alpha	38.85	39.04	32.48	(34.64)	
Voltage					

TM conc. = 10 %,
100%

Suppose u=0.26

Hydrogen strage material 水素吸蔵材料

Hydrogen energy system
水素エネルギー システム

- Decomposition of H_2O by using solar energy → H_2
- Energy storage and transfer in the form of H_2
- Taking out electricity by using fuel cell

→ ‘Greener’ energy cycle (環境に優しいエネルギー サイクル)

→ Hydrogen strage material (水素吸蔵材料)

Design of hydrogen storage materials

Metal hydrates (inorganic hydrogen storage materials)
無機系水素貯蔵材料（金属水素化物）

- High H concentration (高い水素含有量)
- Low price
- Too stable 高温で水素を放出 (安定すぎる)

Metal hydrates	H concentration (weight%)	Formation enthalpy (kJ/mol)
LiH	12.7	-91
NaH	4.2	-56
KH	2.5	-58
MgH ₂	7.6	-76
CaH ₂	4.8	-186

→ Un-stabilize the metal hydrates by doping transition metal impurities
M. Tsuda et al., Thin Solid Films 509 (2006) 157

Formation energy of MgH₂

$$\Delta E = TE(MgH_2 : \text{rutile}) - TE(Mg : hcp) - 2 \times TE(H)$$

- Instead of TE(H₂ molecule), we use TE(H: FCC) to be in consistent with MT approximaion. TE(H)=-1.076 Ry
- Lattice constants of MgH₂, Mg → experimental value
- No-lattice relaxation
 - Calculate how largely we can destabilize MgH₂ by introducing transition metal impurities.
 - Which TM is the most effective ?

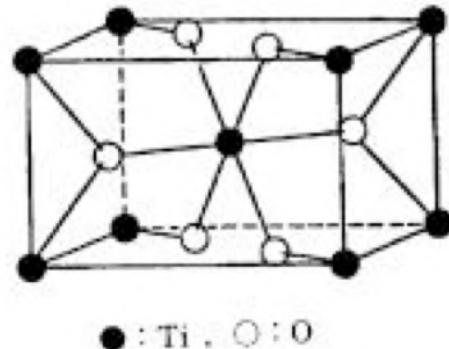


図 1.29 ルチル型構造

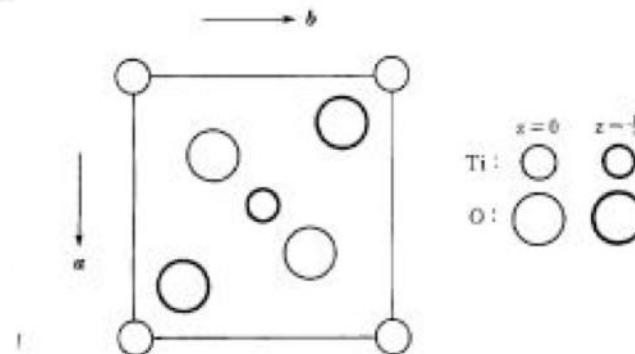


図 1.20 ルチル TiO₂ の結晶構造の c 軸に垂直な面への投影図

MgH₂ :
 $a = 4.501 \text{ \AA}$,
 $c = 3.01 \text{ \AA}$,
 $u = 0.304$

Mg :
 $a = 3.20936 \text{ \AA}$,
 $c = 5.2112 \text{ \AA}$,

Formation energy of MgH₂ with transition metal impurities

$$\Delta E = TE(Mg_{1-x}TM_xH_2 : \text{rutile})$$

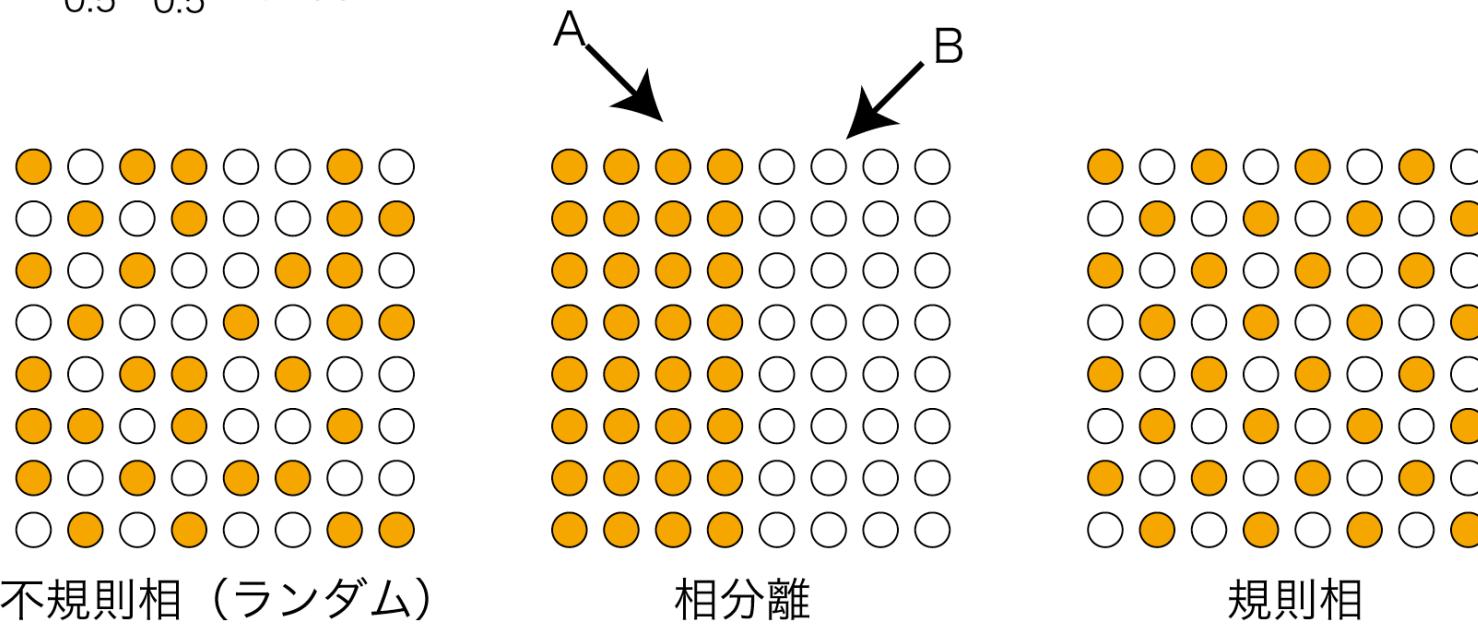
$$-TE(Mg_{1-x}TM_x : hcp) - 2 \times TE(H)$$

1. Calculate ΔE , when transition metal impurity TM (TM=Sc, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn,) are doped in MgH_2 . Suppose $x=0.1$ $\Delta E(MgH_2) = -$

$$\Delta E(MgH_2) = -1.376 eV$$

FCC two-component alloy

A_{0.5}B_{0.5} 二元合金



Soluble

- Ag-Au (), Ag-Pd (), Pd-Pt (), Au-Ni ()

Phase separate

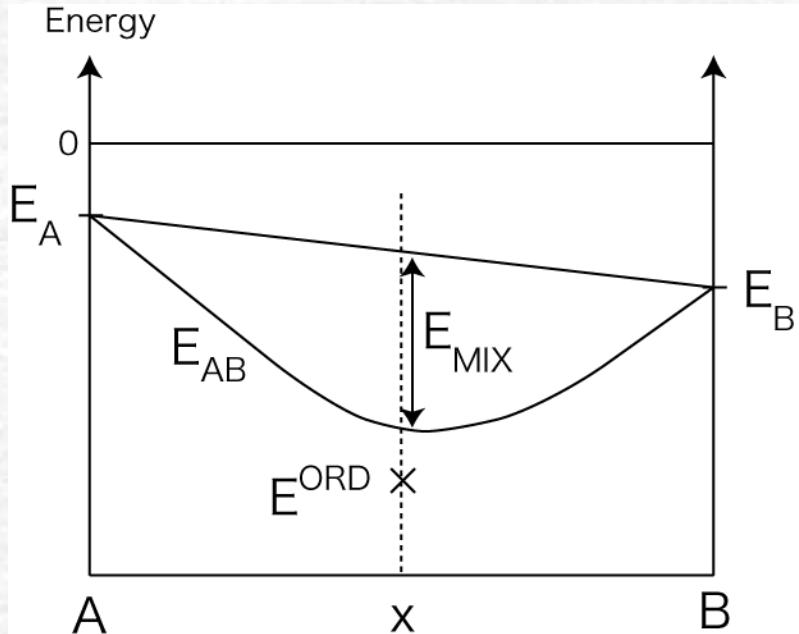
- Cu-Ag (), Au-Pt (), Au-Rh (), Pd-Rh, Pt-Rh

Ordered phase

- Au-Pd, Au-Cu

By using the CPA, all phases (disordered, ordered) can be calculated with in the same framework.

Calculation of mixing energy



E_A : Total energy of A

E_B : Total energy of B

E_{AB} : Total energy of disordered phase

E_{MIX} : Mixing energy

$$= E_{AB} - (1-x)E_A - xE_B$$

x : concentration of B

E_{AB}^{ORD} : Total energy of ordered phase

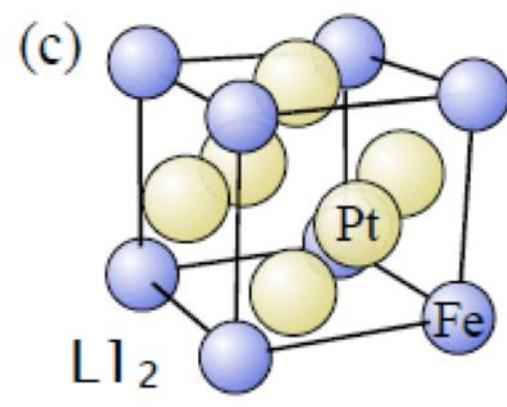
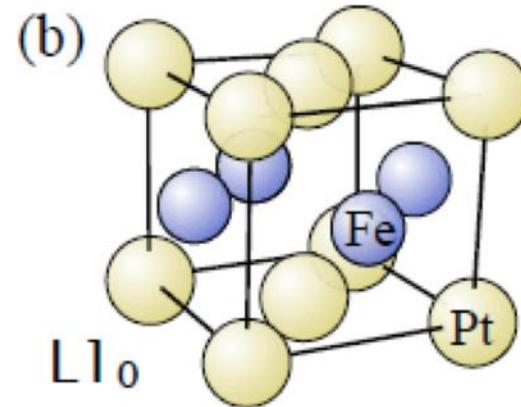
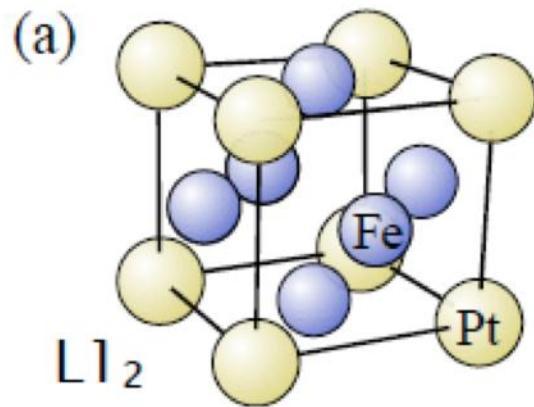
Assumption:

Lattice constants follow the Vegard's law.

$x = 25, 50, 75 \%$

$$a(A_{1-x}B_x) = (1-x) \times a(A) + x \times a(B)$$

$L1_0$, $L1_2$ ordered state



SC

Pt: $(0, 0, 0)$

Fe: $(1/2, 1/2, 0)$,
 $(1/2, 0, 1/2)$,
 $(0, 1/2, 1/2)$

ST

Pt: $(0, 0, 0)$,

Fe: $(1/2, 0, 1/2)$,
 $(0, 1/2, 1/2)$

SC

Fe: $(0, 0, 0)$

Pt: $(1/2, 1/2, 0)$,
 $(1/2, 0, 1/2)$,
 $(0, 1/2, 1/2)$

Assumption:

Lattice constants follow the Vegard's law.

$$a(A_{1-x}B_x) = (1 - x) \times a(A) + x \times a(B)$$